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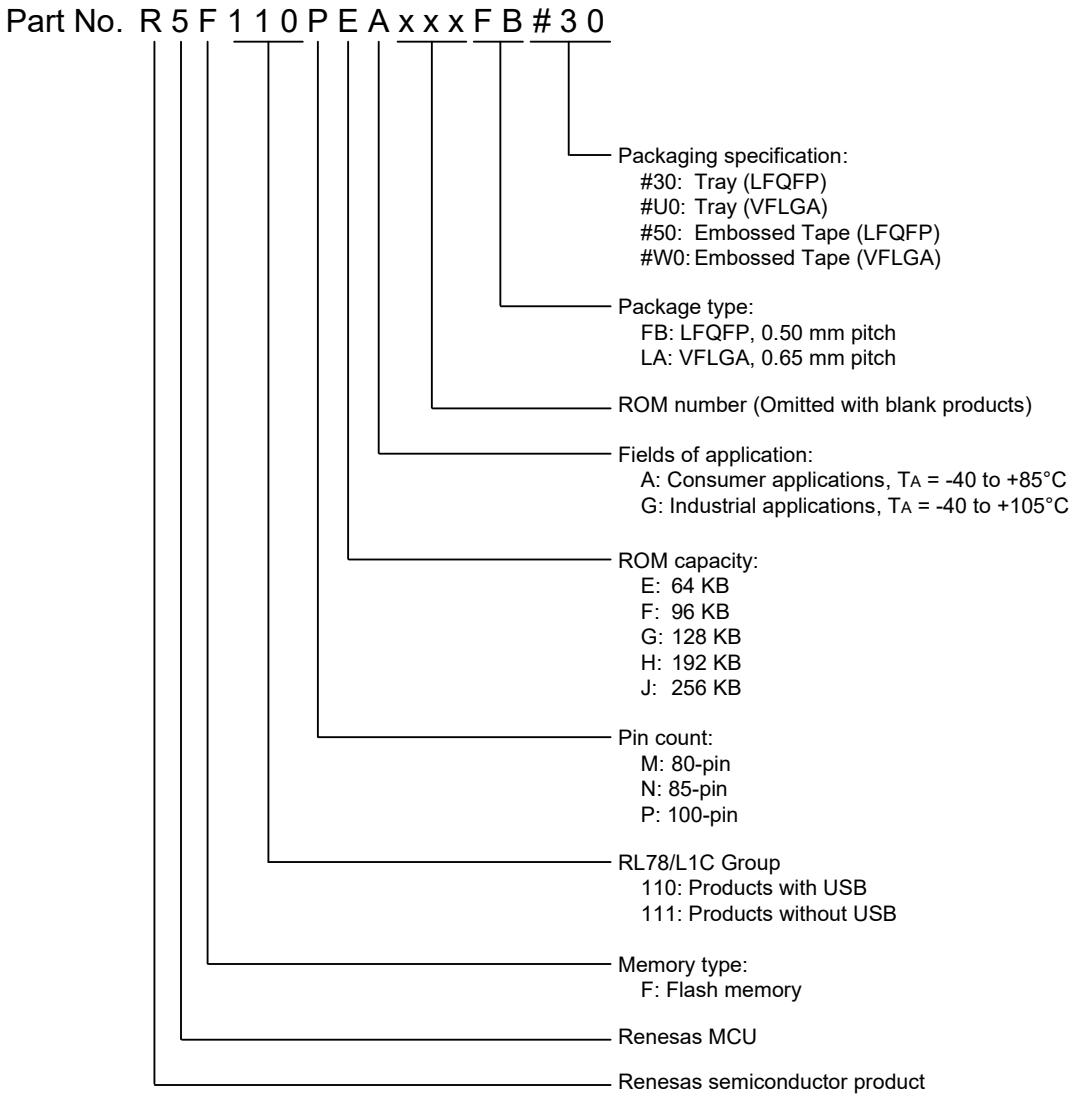
What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	LCD, LVD, POR, PWM, WDT
Number of I/O	55
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 3.6V
Data Converters	A/D 11x8/12b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f111mjafb-30

Figure 1 - 1 Part Number, Memory Size, and Package of RL78/L1C



Caution Orderable part numbers are current as of when this manual was published.
Please make sure to refer to the relevant product page on the Renesas website for the latest part numbers.

[80/85-pin, 100-pin products (without USB)] **(1/2)**

Item		80/85-pin	100-pin
		R5F111Mx/R5F111Nx (x = E to H, J)	R5F111Px (x = E to H, J)
Code flash memory (KB)		64 to 256	64 to 256
Data flash memory (KB)		8	8
RAM (KB)		8 to 16 Note 1	8 to 16 Note 1
Memory space		1 MB	
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) 1 to 20 MHz: VDD = 2.7 to 3.6 V, 1 to 8 MHz: VDD = 1.8 to 2.7 V, 1 to 4 MHz: VDD = 1.6 to 1.8 V	
	High-speed on-chip oscillator clock	HS (high-speed main) operation mode: 1 to 24 MHz (VDD = 2.7 to 3.6 V), HS (high-speed main) operation mode: 1 to 16 MHz (VDD = 2.4 to 3.6 V, LS (low-speed main) operation mode: 1 to 8 MHz (VDD = 1.8 to 3.6 V), LV (low-voltage main) operation mode: 1 to 4 MHz (VDD = 1.6 to 3.6 V)	
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz (TYP.): VDD = 1.6 to 3.6 V	
Low-speed on-chip oscillator clock		15 kHz (TYP.): VDD = 1.6 to 3.6 V	
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)	
Minimum instruction execution time		0.04167 μs (High-speed on-chip oscillator clock: fHOCO = fIH = 24 MHz operation)	
		0.05 μs (High-speed system clock: fMX = 20 MHz operation)	
		30.5 μs (Subsystem clock: fSUB = 32.768 kHz operation)	
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.	
I/O port	Total	63	81
	CMOS I/O	55	73
	CMOS input	5	5
	CMOS output	1	1
	N-ch open-drain I/O (6 V tolerance)	2	2
Timer	16-bit timer TAU	8 channels (with 1 channel remote control output function) (Timer outputs: 8, PWM outputs: 7 Note 2)	
	16-bit timer KB2	3 channels (PWM outputs: 6)	
	Watchdog timer	1 channel	
	12-bit interval timer	1 channel	
	Real-time clock 2	1 channel	
	RTC output	1 1 Hz (subsystem clock: fSUB = 32.768 kHz)	

Note 1. In the case of the 16 KB, this is about 15 KB when the self-programming function and data flash function are used (For details, see **CHAPTER 3** in the RL78/L1C User's Manual).

Note 2. The number of outputs varies, depending on the setting of channels in use and the number of the master.

Note 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the LCD controller/driver, A/D converter, D/A converter, comparator, LVD circuit, USB 2.0 function module, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.

Note 3. When high-speed system clock and subsystem clock are stopped.

Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the real-time clock 2, 12-bit interval timer, and watchdog timer.

Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:	2.7 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 24 MHz
	2.4 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 16 MHz
LS (low-speed main) mode:	1.8 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 8 MHz
LV (low-voltage main) mode	1.6 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 4 MHz

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (48 MHz max.)

Remark 3. f_{IH}: Main system clock source frequency when the high-speed on-chip oscillator clock divided 1, 2, 4, or 8, or the PLL clock divided by 2, 4, or 8 is selected (24 MHz max.)

Remark 4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

Note 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the LCD controller/driver, A/D converter, D/A converter, comparator, LVD circuit, USB 2.0 function module, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

Note 2. During HALT instruction execution by flash memory.

Note 3. When high-speed on-chip oscillator and subsystem clock are stopped.

Note 4. When high-speed system clock and subsystem clock are stopped.

Note 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the real-time clock 2 is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.

Note 6. Not including the current flowing into the real-time clock 2, 12-bit interval timer, and watchdog timer.

Note 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 24 MHz
2.4 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 16 MHz
LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 8 MHz
LV (low-voltage main) mode 1.6 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 4 MHz

Note 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

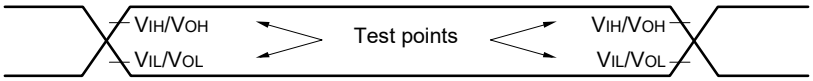
Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (48 MHz max.)

Remark 3. f_{IH}: Main system clock source frequency when the high-speed on-chip oscillator clock divided 1, 2, 4, or 8, or the PLL clock divided by 2, 4, or 8 is selected (24 MHz max.)

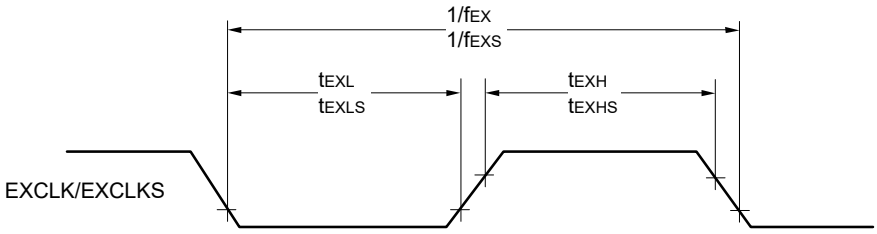
Remark 4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

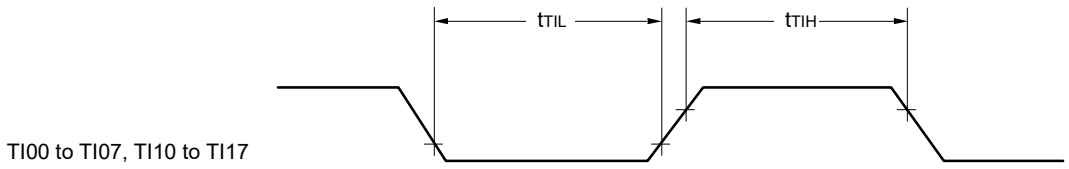
AC Timing Test Points

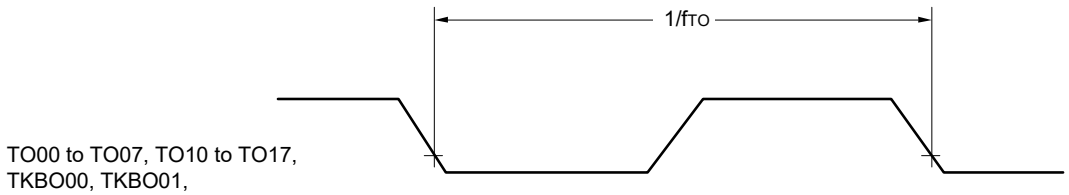


External System Clock Timing

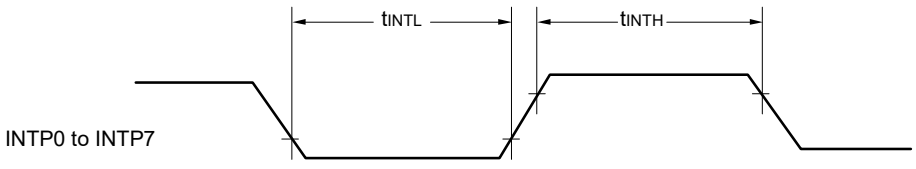


TI/TO Timing

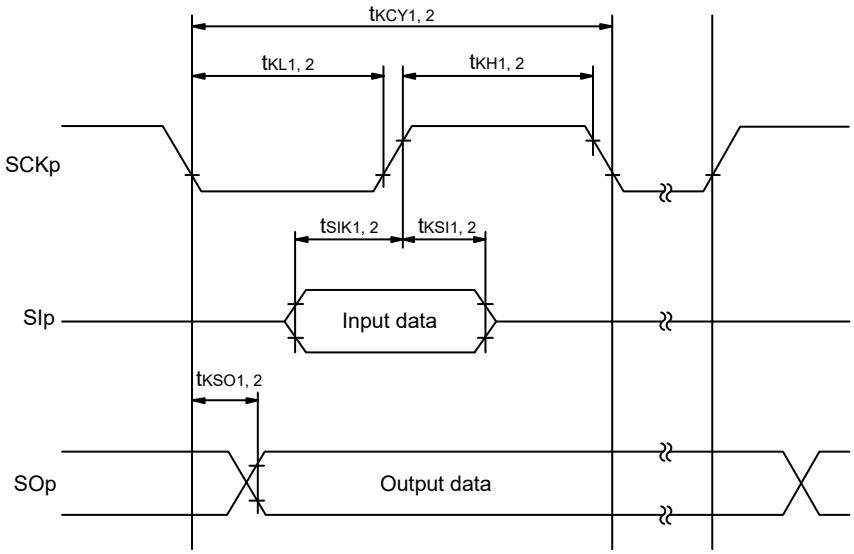




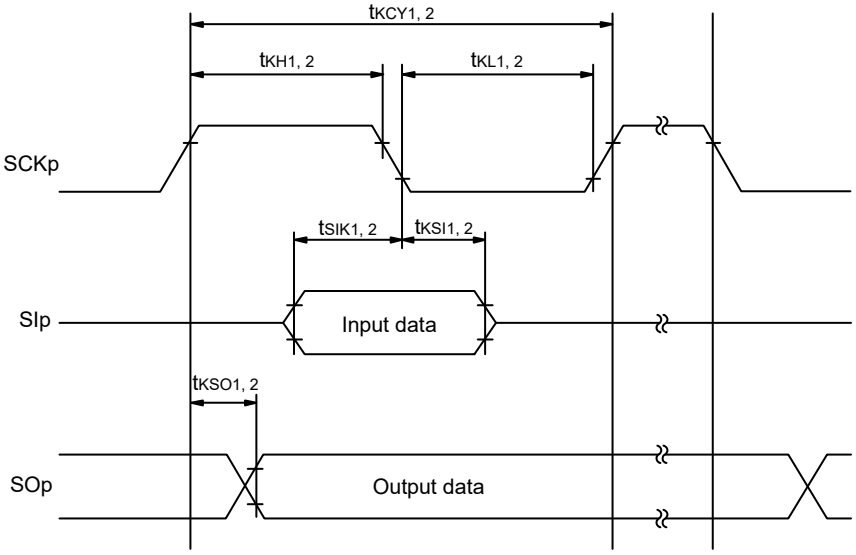
Interrupt Request Input Timing



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 10, 20, 30)
Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(3) BC option standard

(T_A = -40 to +85°C, 4.35 V ≤ UV_{BUS} ≤ 5.25 V, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V, HS (High-speed main) mode only)

Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit
UDP/UDM input reference voltage (UV_{BUS} divider ratio) (Function)	VDSELi [3: 0] (i = 0, 1)	0000	V_{DDET0}		27	32	37	%UVBUS
		0001	V_{DDET1}		29	34	39	%UVBUS
		0010	V_{DDET2}		32	37	42	%UVBUS
		0011	V_{DDET3}		35	40	45	%UVBUS
		0100	V_{DDET4}		38	43	48	%UVBUS
		0101	V_{DDET5}		41	46	51	%UVBUS
		0110	V_{DDET6}		44	49	54	%UVBUS
		0111	V_{DDET7}		47	52	57	%UVBUS
		1000	V_{DDET8}		51	56	61	%UVBUS
		1001	V_{DDET9}		55	60	65	%UVBUS
		1010	V_{DDET10}		59	64	69	%UVBUS
		1011	V_{DDET11}		63	68	73	%UVBUS
		1100	V_{DDET12}		67	72	73	%UVBUS
		1101	V_{DDET13}		71	76	81	%UVBUS
		1110	V_{DDET14}		75	80	85	%UVBUS
		1111	V_{DDET15}		79	84	89	%UVBUS

2.6.4 Comparator

(T_A = -40 to +85°C, 1.6 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage range	Ivref			0		V_{DD} - 1.4	V
	Ivcmp			-0.3		V_{DD} + 0.3	V
Output delay	td	V_{DD} = 3.0 V Input slew rate > 50 mV/μs	High-speed comparator mode, standard mode			1.2	μs
			High-speed comparator mode, window mode			2.0	μs
			Low-speed comparator mode, standard mode		3	5.0	μs
High-electric-potential judgment voltage	VTW+	High-speed comparator mode, window mode			0.76 V_{DD}		V
Low-electric-potential judgment voltage	VTW-	High-speed comparator mode, window mode			0.24 V_{DD}		V
Operation stabilization wait time	t_{CMP}			100			μs
Internal reference voltage Note	V_{BGR}			1.38	1.45	1.50	V

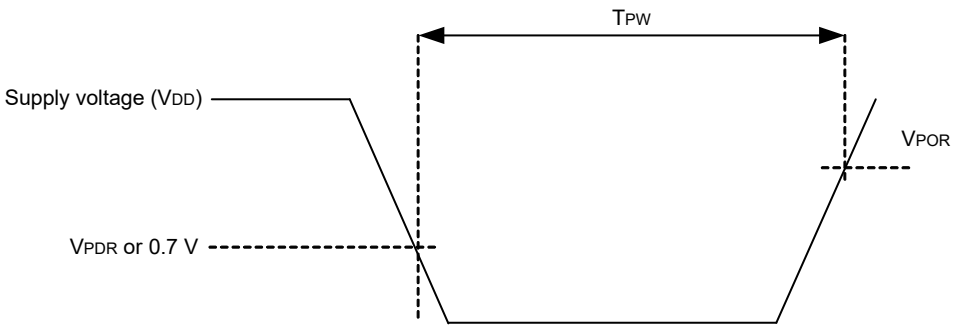
Note Not usable in LS (low-speed main) mode, LV (low-voltage main) mode, sub-clock operation, or STOP mode.

2.6.5 POR circuit characteristics

(T_A = -40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	1.47	1.51	1.55	V
	V_{PDR}	Power supply fall time Note	1.46	1.50	1.54	V
Minimum pulse width	T_{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



(2) 1/4 bias method

(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	V_{L1}	C1 to C4 Note 1 = 0.47 μF Note 2	VLCD = 04H	0.90	1.00	1.08	V
			VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
Doubler output voltage	V_{L2}	C1 to C4 Note 1 = 0.47 μF		2 V_{L1} - 0.08	2 V_{L1}	2 V_{L1}	V
Tripler output voltage	V_{L3}	C1 to C4 Note 1 = 0.47 μF		3 V_{L1} - 0.12	3 V_{L1}	3 V_{L1}	V
Quadruply output voltage	V_{L4}	C1 to C5 Note 1 = 0.47 μF		4 V_{L1} - 0.16	4 V_{L1}	4 V_{L1}	V
Reference voltage setup time Note 2	t_{VWAIT1}			5			ms
Voltage boost wait time Note 3	t_{VWAIT2}	C1 to C5 Note 1 = 0.47μF		500			ms

Note 1. This is a capacitor that is connected between voltage pins used to drive the LCD.
C1: A capacitor connected between CAPH and CAPL
C2: A capacitor connected between V_{L1} and GND
C3: A capacitor connected between V_{L2} and GND
C4: A capacitor connected between V_{L3} and GND
C5: A capacitor connected between V_{L4} and GND
C1 = C2 = C3 = C4 = 0.47 μF±30%

Note 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).

Note 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

2.8.3 Capacitor split method

(1) 1/3 bias method

(T_A = -40 to +85°C, 2.2 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
V_{L4} voltage	V_{L4}	C1 to C4 = 0.47 μF Note 2		V_{DD}		V
V_{L2} voltage	V_{L2}	C1 to C4 = 0.47 μF Note 2	2/3 V_{L4} - 0.1	2/3 V_{L4}	2/3 V_{L4} + 0.1	V
V_{L1} voltage	V_{L1}	C1 to C4 = 0.47 μF Note 2	1/3 V_{L4} - 0.1	1/3 V_{L4}	1/3 V_{L4} + 0.1	V
Capacitor split wait time Note 1	t_{VWAIT}		100			ms

Note 1. This is the wait time from when voltage bucking is started (VLCON = 1) until display is enabled (LCDON = 1).

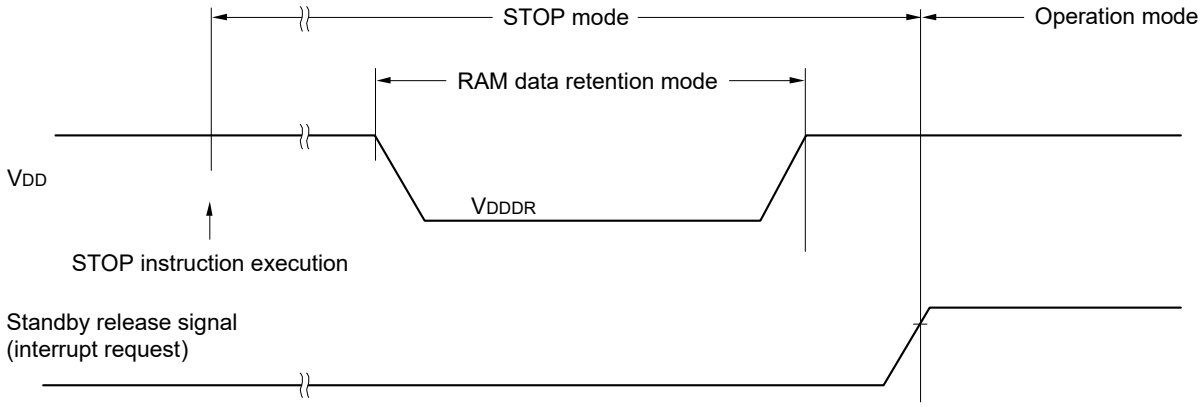
Note 2. This is a capacitor that is connected between voltage pins used to drive the LCD.
C1: A capacitor connected between CAPH and CAPL
C2: A capacitor connected between V_{L1} and GND
C3: A capacitor connected between V_{L2} and GND
C4: A capacitor connected between V_{L4} and GND
C1 = C2 = C3 = C4 = 0.47 μF±30%

2.9 RAM Data Retention Characteristics

(T_A = -40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.46 Note		3.6	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



2.10 Flash Memory Programming Characteristics

(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	f_{CLK}	2.4 V ≤ V_{DD} ≤ 3.6 V	1		24	MHz
Number of code flash rewrites Notes 1, 2, 3	C_{erwr}	Retained for 20 years T_A = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year T_A = 25°C		1,000,000		
		Retained for 5 years T_A = 85°C	100,000			
		Retained for 20 years T_A = 85°C	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.11 Dedicated Flash Memory Programmer Communication (UART)

(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

(T_A = -40 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

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Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	I_{OL1}	Per pin for P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143				8.5 Note 2	mA
		Per pin for P60 and P61				15.0 Note 2	mA
		Total of P40 to P46, P130 (When duty ≤ 70% Note 3)	2.7 V ≤ V_{DD} ≤ 3.6 V			15.0	mA
			2.4 V ≤ V_{DD} < 2.7 V			9.0	mA
		Total of P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P140 to P143 (When duty ≤ 70% Note 3)	2.7 V ≤ V_{DD} ≤ 3.6 V			35.0	mA
			2.4 V ≤ V_{DD} < 2.7 V			20.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				50.0	mA
	I_{OL2}	Per pin for P150 to P156				0.4 Note 2	mA
		Total of all pins	2.4 V ≤ V_{DD} ≤ 3.6 V			2.8	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the V_{SS} pin.

Note 2. However, do not exceed the total current value.

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Note 3. Specification under conditions where the duty factor ≤ 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression

(when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OL} = 10.0 mA

Total output current of pins = (10.0 × 0.7)/(80 × 0.01) ≈ 8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Input leakage current, high	I_{LIH1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P137, P140 to P143, $\overline{RESET}$	V_I = V_{DD}				1	μA
	I_{LIH2}	P20, P21, P140 to P143	V_I = V_{DD}				1	μA
	I_{LIH3}	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	V_I = V_{DD}	In input port or external clock input			1	μA
				In resonator connection			10	μA
	I_{LIH4}	P150 to P156	V_I = AV_{DD}				1	μA
Input leakage current, low	I_{LIL1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P137, P140 to P143, $\overline{RESET}$	V_I = V_{SS}				-1	μA
	I_{LIL2}	P20, P21, P140 to P143	V_I = V_{SS}				-1	μA
	I_{LIL3}	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	V_I = V_{SS}	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
	I_{LIL4}	P150 to P156	V_I = AV_{SS}				-1	μA
On-chip pull-up resistance	R_{U1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P70 to P77, P140 to P143, P125 to P127	V_I = V_{SS}	2.4 V ≤ V_{DD} ≤ 3.6 V	10	20	100	kΩ
	R_{U2}	P40 to P46, P80 to P83	V_I = V_{SS}		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.4 AC Characteristics

3.4.1 Basic operation

(T_A = -40 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V) **(1/2)**

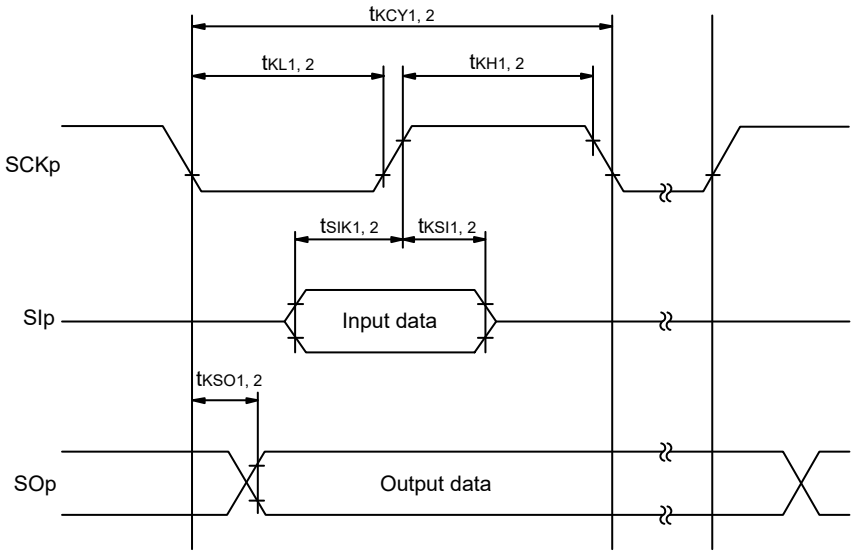
Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V	0.0417		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
		Subsystem clock (f_{SUB}) operation		2.4 V ≤ V_{DD} ≤ 3.6 V	28.5	30.5	31.3	μs
		In the self-programming mode	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V	0.0417		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
External main system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 3.6 V			1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V			1.0		16.0	MHz
	f_{EXT}				32		35	kHz
External main system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 3.6 V			24			ns
		2.4 V ≤ V_{DD} < 2.7 V			30			ns
	t_{EXHS}, t_{EXLS}				13.7			μs
TI00 to TI07 input high-level width, low-level width	t_{TIH}, t_{TIL}				1/f_{MCK} + 10			ns

Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 7))

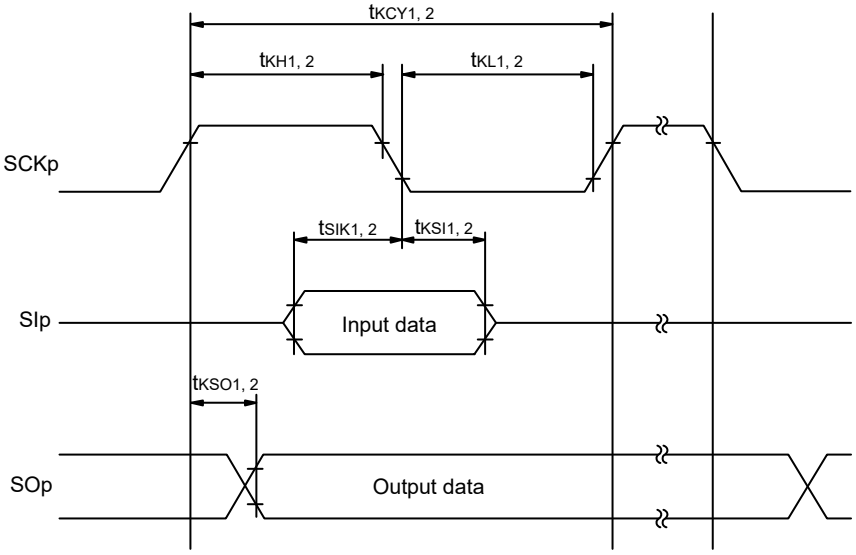
(T_A = -40 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V) **(2/2)**

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
TO00 to TO07, TKBO00, TKBO01, TKBO10, TKBO11, TKBO20, TKBO21 output frequency	f_{TO}	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V			8	MHz
			2.4 V ≤ V_{DD} < 2.7 V			8	MHz
PCLBUZ0, PCLBUZ1 output frequency	f_{PCL}	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V			8	MHz
			2.4 V ≤ V_{DD} < 2.7 V			8	MHz
Interrupt input high-level width, low-level width	t_{INTH}, t_{INTL}	INTP0 to INTP7	2.4 V ≤ V_{DD} ≤ 3.6 V	1			µs
Key interrupt input low-level width	t_{KR}	2.4 V ≤ V_{DD} ≤ 3.6 V		250			ns
TMKB2 forced output stop input high-level width	t_{IHR}	INTP0 to INTP7	f_{CLK} > 16 MHz	125			ns
			f_{CLK} ≤ 16 MHz	2			f_{CLK}
$\overline{RESET}$ low-level width	t_{RSL}			10			µs

CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

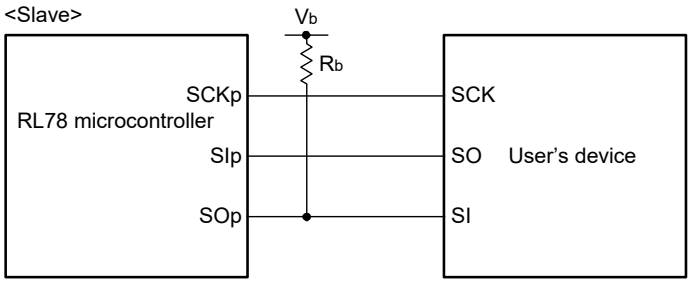


CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 10, 20, 30)
Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

CSI mode connection diagram (during communication at different potential)



Remark 1. Rb[Ω]: Communication line (SOp) pull-up resistance, Cb[F]: Communication line (SOp) load capacitance, Vb[V]: Communication line voltage

Remark 2. p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 3. fMCK: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 02, 10, 12))

(4) When reference voltage (+) = AV_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AV_{SS} (ADREFM = 0), conversion target: ANI16 to ANI21, internal reference voltage, temperature sensor output voltage

(T_A = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 3.6 V, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{DD}, Reference voltage (-) = AV_{SS} = 0)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AV_{DD} ≤ 3.6 V	8		12	bit
Overall error Note 1	AINL	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±8.5	LSB
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V	4.125			µs
Zero-scale error Note 1	EZS	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±8.0	LSB
Full-scale error Note 1	EFS	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±8.0	LSB
Integral linearity error Note 1	ILE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±3.5	LSB
Differential linearity error Note 1	DLE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±2.5	LSB
Analog input voltage	VAIN			0		AV_{DD}	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode)		V_{BGR} Note 2			
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode)		V_{TMP25} Note 2			

Note 1. Excludes quantization error (±1/2 LSB).

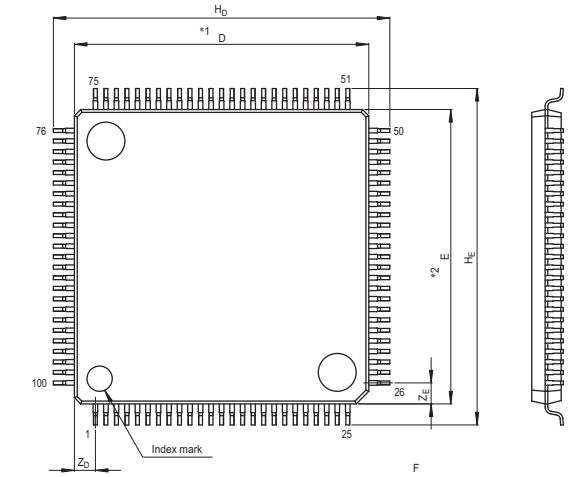
Note 2. Refer to **3.6.2 Temperature sensor, internal reference voltage output characteristics**.

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

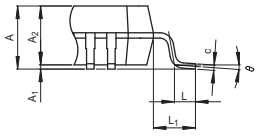
4.3 100-pin products

R5F110PEAFB, R5F110PFAFB, R5F110PGAFB, R5F110PHAFB, R5F110PJAFB
R5F111PEAFB, R5F111PFAFB, R5F111PGAFB, R5F111PHAFB, R5F111PJAFB
R5F110PEGFB, R5F110PFGFB, R5F110PGGFB, R5F110PHGFB, R5F110PJGFB
R5F111PEGFB, R5F111PFGFB, R5F111PGGFB, R5F111PHGFB, R5F111PJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LFQFP100-14x14-0.50	PLQP0100KB-A	100P6Q-A / FP-100U / FP-100UV	0.6g



Terminal cross section



Detail F

NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	13.9	14.0	14.1
E	13.9	14.0	14.1
A_2	—	1.4	—
H_D	15.8	16.0	16.2
H_E	15.8	16.0	16.2
A	—	—	1.7
A_1	0.05	0.1	0.15
b_p	0.15	0.20	0.25
b_1	—	0.18	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.08
Z_D	—	1.0	—
Z_E	—	1.0	—
L	0.35	0.5	0.65
L_1	—	1.0	—

REVISION HISTORY	RL78/L1C Datasheet

Rev.	Date	Description	
		Page	Summary
0.01	Oct 15, 2012	—	First Edition issued
1.00	Nov 18, 2013	1, 2	Modification of 1.1 Features
		3, 4	Modification of 1.2 Ordering Information
		5 to 8	Modification of package type in 1.3 Pin Configuration (Top View)
		14 to 17	Modification of vectored interrupt sources in 1.6 Outline of Functions
		14 to 17	Modification of operating ambient temperature in 1.6 Outline of Functions
		19 to 21	Modification of description in tables in 2.1 Absolute Maximum Ratings
		22, 23	Modification of description in 2.2 Oscillator Characteristics
		25	Modification of low-level output current in 2.3.1 Pin characteristics
		26	Modification of error of high-level input voltage conditions in 2.3.1 Pin characteristics
		26	Modification of error of low-level input voltage conditions in 2.3.1 Pin characteristics
		27	Modification of low-level output voltage in 2.3.1 Pin characteristics
		28	Modification of error of internal pull-up resistor conditions in 2.3.1 Pin characteristics
		29 to 34	Modification of 2.3.2 Supply current characteristics
		35, 36	Modification of 2.4 AC Characteristics
		37, 38	Addition of minimum instruction execution time during main system clock operation
		41 to 63	Addition of LS mode and LV mode characteristics in 2.5.1 Serial array unit
		64 to 66	Addition of LS mode and LV mode characteristics in 2.5.2 Serial interface IICA
		67, 68	Modification of conditions in 2.5.3 USB
		69	Addition of (3) BC option standard in 2.5.3 USB
		70 to 75	Addition of characteristics about conversion of internal reference voltage and temperature sensor in 2.6.1 A/D converter characteristics
		76	Addition of characteristic in 2.6.4 Comparator
		76	Deletion of detection delay in 2.6.5 POR circuit characteristics
		78	Modification of 2.7 Power supply voltage rising slope characteristics
		79 to 82	Modification of 2.8 LCD Characteristics
		83	Modification of 2.9 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics
		83	Modification of 2.10 Flash Memory Programming Characteristics
		84	Addition of 2.12 Timing Specs for Switching Modes
		85 to 144	Addition of 3. ELECTRICAL SPECIFICATIONS (G: T_A = -40 to +105°C)
2.00	Feb 21, 2014	All	Addition of 85-pin product information
		All	Modification from 80-pin to 80/85-pin
		All	Modification from x = M, P to x = M, N, P
		All	Modification from high-accuracy real-time clock to real-time clock 2
		All	Modification from RTC to RTC2
		1	Modification of 1.1 Features
		3	Modification of 1.2 Ordering Information